

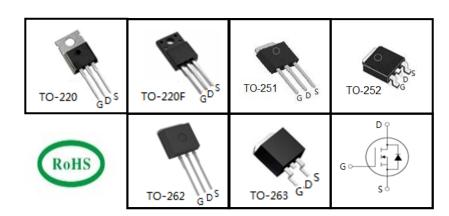
500V Super-Junction Power MOSFET

FEATURES

- $\bullet \quad \text{Very low FOM R}_{\text{DS(on)}} \times \text{Q}_{\text{g}} \\$
- 100% avalanche tested
- RoHS compliant

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information						
Device	TPP50R400C	TPA50R400C	TPU50R400C	TPD50R400C	TPC50R400C	TPB50R400C
Package	TO-220	TO-220F	TO-251	TO-252	TO-262	TO-263
Marking	50R400C	50R400C	50R400C	50R400C	50R400C	50R400C

Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted						
_		Value				
Parameter	Symbol	TO-220, TO-251, TO-252 TO-262, TO-263	TO-220F	Unit		
Drain-Source Voltage (V _{GS} = 0V)	V_{DSS}	500		V		
Continuous Drain Current	I _D	7		Α		
Pulsed Drain Current (note1)	I _{DM}	21		Α		
Gate-Source Voltage	V_{GSS}	±30		V		
Single Pulse Avalanche Energy (note2)	E _{AS}	162		mJ		
Avalanche Current (note1)	I _{AR}	1.4		Α		
Repetitive Avalanche Energy (note1)	E _{AR}	0.2		mJ		
Power Dissipation (T _C = 25°C)	P _D	63 28		W		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C		

Thermal Resistance						
		Value				
Parameter	Symbol	TO-220, TO-251, TO-252 TO-262, TO-263	TO-220F	Unit		
Thermal Resistance, Junction-to-Case	R _{thJC}	2.0	4.5	°C/W		
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62	80	30/00		

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${\tt TPP50R400C, TPA50R400C, TPU50R400C, TPD50R400C, TPC50R400C, TPB50R400C, T$

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Devemates		T	Value				
Parameter	Symbol Test Conditions		Min.	Тур.	Max.	Unit	
Static		•					
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 250\mu A$	500			V	
Zara Cata Valtaga Drain Current		$V_{DS} = 500V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 500V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100	μA	
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30V$			±100	nA	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4.0	V	
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_{D} = 3A$		0.36	0.40	Ω	
Forward Transconductance (Note3)	g _{fs}	$V_{DS} = 10V, I_{D} = 3A$		5		S	
Dynamic		•					
Input Capacitance	C _{iss}	V - 0V		587		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 50V,$		31			
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		4			
Total Gate Charge	Q_g			14.5		nC	
Gate-Source Charge	Q_{gs}	$V_{DD} = 400 \text{V}, I_{D} = 7 \text{A}, $ $V_{GS} = 10 \text{V}$		3			
Gate-Drain Charge	Q_{gd}			5.2			
Turn-on Delay Time	t _{d(on)}			39			
Turn-on Rise Time	t _r	$V_{DD} = 400V, I_{D} = 7A,$		25			
Turn-off Delay Time	t _{d(off)}	$R_G = 25\Omega$		100		ns	
Turn-off Fall Time	t _f			18			
Drain-Source Body Diode Characteris	stics						
Continuous Body Diode Current	Is	T 0500			6.3	^	
Pulsed Diode Forward Current	I _{SM}	T _C = 25°C			19	Α	
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C$, $I_{SD} = 7A$, $V_{GS} = 0V$		0.9	1.2	V	
Reverse Recovery Time	t _{rr}			250		ns	
Reverse Recovery Charge	Q _{rr}	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$		2.1		μC	
Peak Reverse Recovery Current	I _{rrm}	,		16		Α	

Notes

- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2. I_{AS} = 1.4A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 1%

Typical Characteristics $T_1 = 25^{\circ}$ C, unless otherwise noted

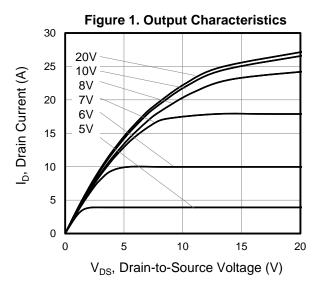


Figure 3. On-Resistance vs. Drain Current

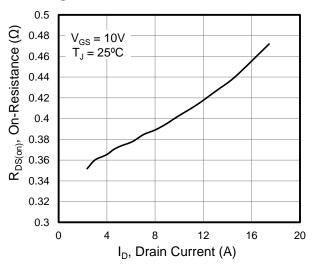


Figure 5. Gate Charge

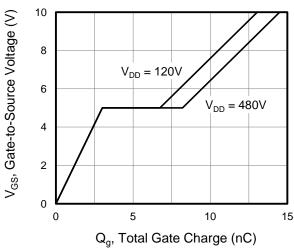


Figure 2. Transfer Characteristics

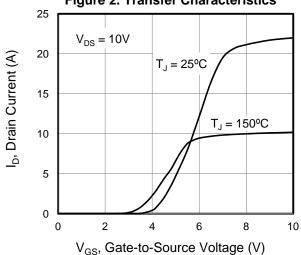


Figure 4. Capacitance

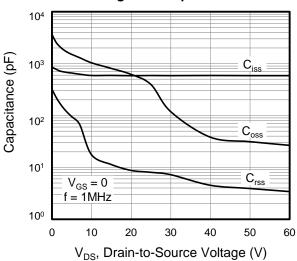
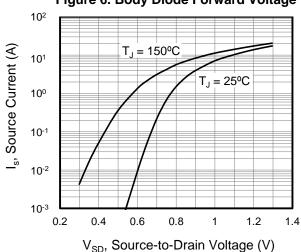
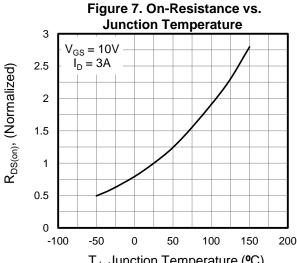


Figure 6. Body Diode Forward Voltage

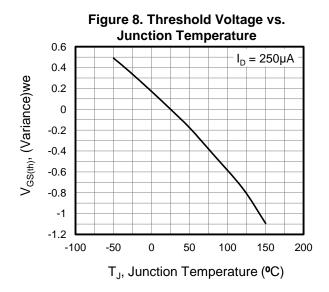


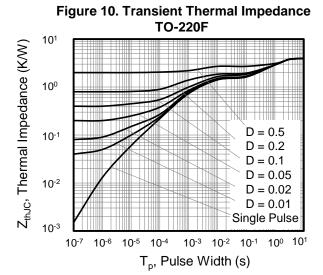
Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted



T_J, Junction Temperature (°C)

Figure 9. Transient Thermal Impedance TO-220,TO-251,TO-252,TO-262,TO-263 Z_{thJC}, Thermal Impedance (K/W) 10¹ 10⁰ 10-1 D = 0.5D = 0.2D = 0.1D = 0.0510-2 D = 0.02D = 0.01Single Pulse 10-3 10-5 10-2 10-1 T_n, Pulse Width (s)





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Figure A: Gate Charge Test Circuit and Waveform

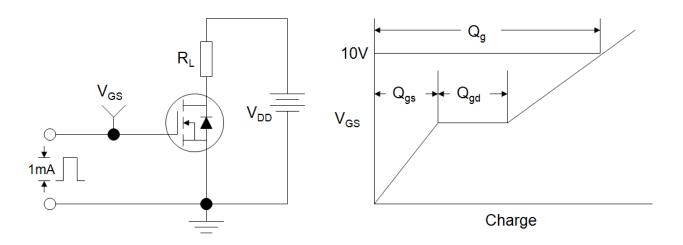


Figure B: Resistive Switching Test Circuit and Waveform

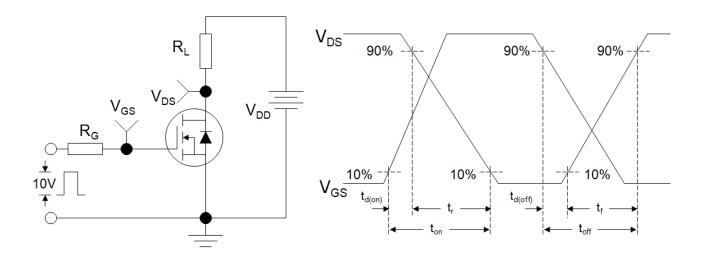
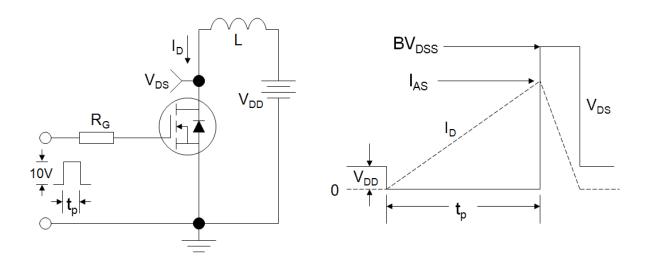


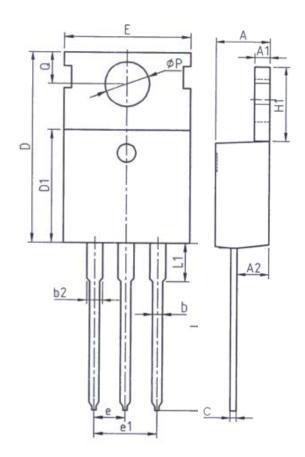
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

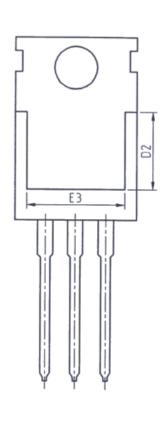


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TO-220



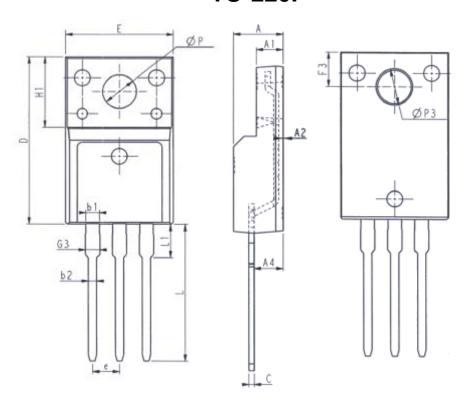


Unit: mm					
Symbol	Min.	Max.			
Α	4. 37	4. 77			
A1	1. 25	1. 45			
A2	2. 20	2. 60			
b	0. 70	0. 95			
b2	1. 17	1. 47			
С	0. 40	0. 65			
D	15. 10	16. 10			
D1	8. 80	9. 40			
D2	5. 50	_			

Unit: mm					
Symbol	Min. Max.				
E	9. 70	10.30			
E3	7. 00	-			
е	2. 54BSC				
e1	5. 08	BBSC			
H1	6. 25	6. 85			
L	12. 75	13.80			
L1	_	3. 40			
Р	3. 40	3. 80			
Q	2. 60	3. 00			



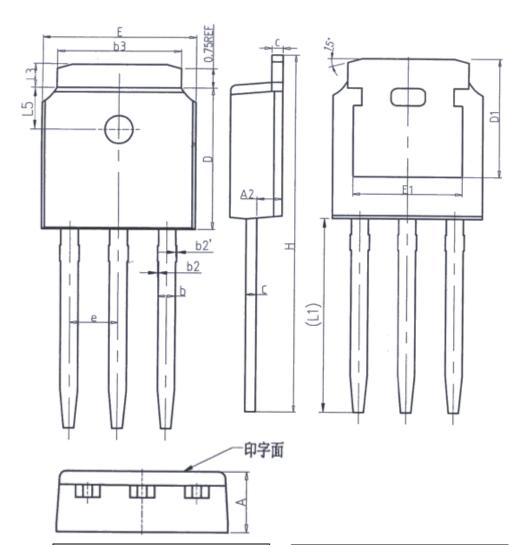
TO-220F



l	Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.	
E	9. 96	10.36	L	12. 68	13. 28	
Α	4. 50	4. 90	L1	2. 93	3. 13	
A1	2. 34	2. 74	Р	3. 03	3. 38	
A2	0. 30	0.60	Р3	3. 15	3. 65	
A4	2. 56	2. 96	F3	3. 15	3. 45	
С	0.40	0. 65	G3	1. 25	1. 55	
D	15. 57	16. 17	b1	1. 18	1. 43	
H1	6. 70REF		b2	0. 70	0. 95	
е	2. 54BSC					



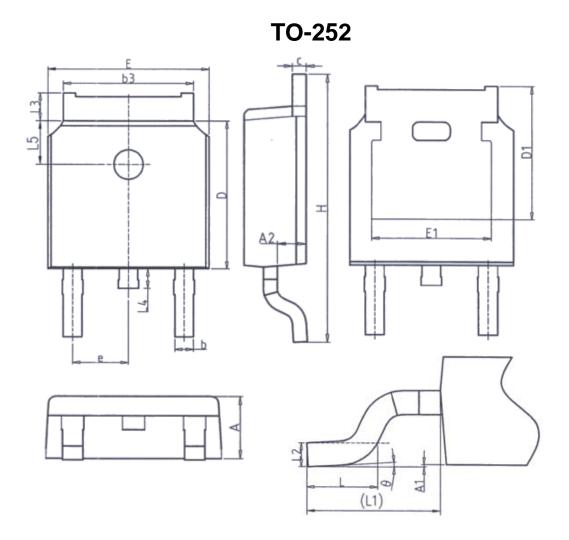
TO-251



Unit: mm					
Symbol	Symbol Min.				
Α	2. 20	2. 40			
A2	0. 97	1. 17			
b	0. 68	0.90			
b2	0.00	0.10			
b2′	0.00	0.10			
b3	5. 20	5. 50			
С	0. 43	0. 63			
D	5. 98	6. 22			

Unit: mm					
Symbol	Min.	Max.			
D1	5. 30	REF			
E	6. 40	6. 80			
E1	4. 63	-			
е	2. 286BSC				
Н	16. 22	16. 82			
L1	9. 15	9. 65			
L3	0.88	1. 28			
L5	1. 65	1. 95			

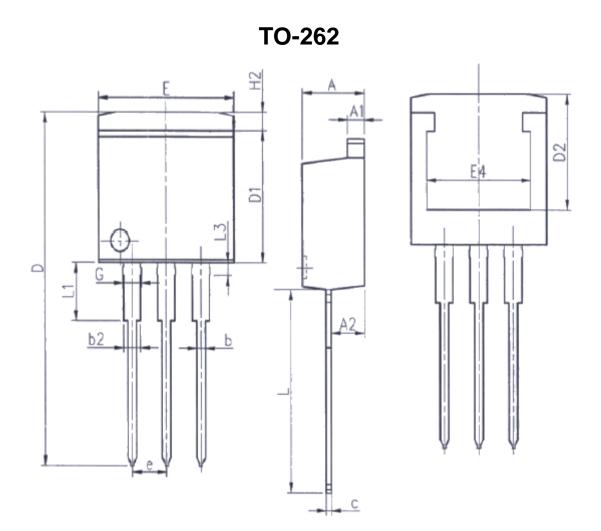




Unit: mm						
Symbol	Min.	Max.				
Α	2. 20	2. 40				
A1	0.00	0. 20				
A2	0. 97	1. 17				
b	0. 68	0. 90				
b3	5. 20	5. 50				
С	0. 43	0. 63				
D	5. 98	6. 22				
D1 5. 30REF						
E	6. 40	6. 80				
E1	4. 63	_				

Unit: mm					
Symbol	Min.	Max.			
е	2. 28	6BSC			
Н	9. 40	10.50			
L	1. 38	1. 75			
L1	2. 90REF				
L2	0. 51	IBSC			
L3	0.88	1. 28			
L4	- 1.00				
L5	1.65 1.95				
θ	θ 0° 8°				



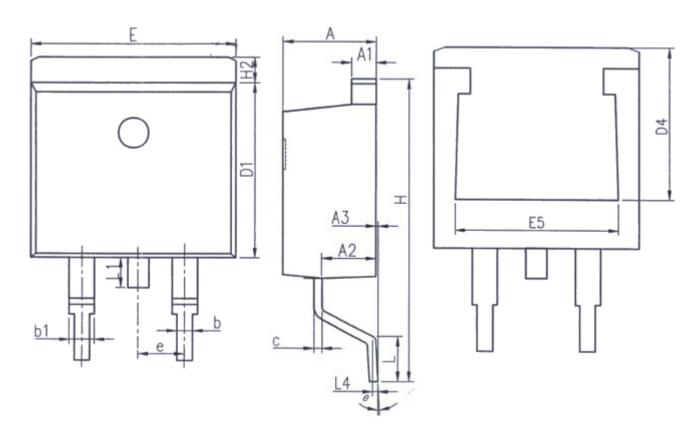


Unit: mm					
Symbol	Min.	Max.			
Α	4. 37	4. 77			
A1	1. 22	1. 42			
A2	2. 47	2. 87			
b	0. 70	0. 97			
b2	1. 17	1. 42			
С	0. 28	0.53			
D	23. 20	24. 02			
D1	8. 38	8. 90			
D2	6. 00	-			

Unit: mm			
Symbol	Min.	Max.	
E	9. 90	10. 39	
E4	7. 30	_	
e	2. 54BSC		
G	1. 25	1.50	
H2	-	1. 31	
L	13. 34	14. 10	
L1	3. 30	4. 06	
L3	0. 95	1. 15	

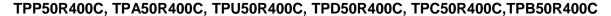


TO-263



Unit: mm		
Symbol	Min.	Max.
Α	4. 37	4. 77
A 1	1. 22	1. 42
A2	2. 49	2. 89
A3	0. 00	0. 25
b	0. 70	0. 96
b1	1. 17	1. 47
С	0. 30	0. 53
D1	8. 50	8. 90
D4	6. 60	_

Unit: mm			
Symbol	Min.	Max.	
E	9.86	10.36	
E 5	7. 06	-	
e	2. 54BSC		
Н	14. 70	15. 50	
H2	1. 07	1. 47	
L	2.00	2. 60	
L1	1. 40	1. 70	
L4	0. 25BSC		
θ	0°	9°	





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